

ABSTRACT

The present invention provides: a reflective mask blank which is capable of accurately transferring a pattern to a transfer-receiving body; a reflective mask; and a method for producing a semiconductor device. A reflective mask blank (100) according to the present invention comprises: a substrate (10); a multilayer reflective film (12) which is formed on the substrate (10) and reflects EUV light; and a laminate film (16) which is formed on the multilayer reflective film (12). The laminate film (16) has an absolute reflectance of 2.5% or less with respect to EUV light, and comprises a first layer (18) and a second layer (20) that is formed on the first layer (18); and the first layer (18) comprises a phase shift film which shifts the phase of EUV light. Alternatively, the laminate film (16) is a phase shift film which comprises a first layer (18) and a second layer (20) that is formed on the first layer (18), and which shifts the phase of EUV light; and the first layer (18) comprises an absorption layer that has an absolute reflectance of 2.5% or less with respect to EUV light.